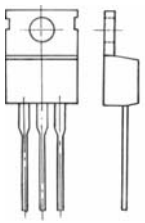
Transys Electronics LIMITED

TO-220 Plastic-Encapsulated Transistors

2SB834 TRANSISTOR (PNP)

TO-220

1. BASE
2. COLLECTOR
3. EMITTER



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FEATURES

Power dissipation

P_{CM}: 1.5 W (Tamb=25℃)

Collector current

I_{CM}: -3 A

Collector-base voltage

$V_{(BR)CBO}$: -60 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=-100μA, I_E=0	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic=-50mA, I_B=0	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA, I_C=0	-7			V
Collector cut-off current	I_{CBO}	V_{CB}=-60V, I_E=0			-100	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-7V, I_C=0			-100	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-5V, I_C=-500mA	60		200	
	$h_{FE(2)}$	V_{CE}=-5V, I_C=-3A	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-3A, I_B=-0.3A			-1	V
Base-emitter voltage	V_{BE}	V_{CE}=-5V, I_C=-500mA			-1	V
Transition frequency	f_T	V_{CE}=-5V,I_C=-500mA		9		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz		150		pF
Turn-on Time	t_{on}	V_{CC}=-30V, I_c=-2A, I_{B1}=I_{B2}=-0.2A		0.4		μs
Storage Time	t_{stg}			1.7		μs
Turn-off Time	t_{off}			0.5		μs

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	60-120	100-200